

**1. Scope :**

This specification applies to silicon non-zero-crossing phototriac chips,  
Device No. ST-1127S

**2. Structure :**

- 2-1. Planar type .
- 2-2. Electrodes :aluminum alloy

**3. Size :**

- 3-1. Chip size : 40 mils × 40 mils (1.016 mm ×1.016mm ).
- 3-2. Chip thickness : 12±1.5 mil (0.305± 0.038 mm ).
- 3-3. Pad area : 6 mil dia (0.152 mm dia ).
- 3-4. Pattern drawing : refer to the attached drawing.

**4. Electro-optical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Peak blocking Current	$I_{DRM}$	$V_{DRM}=800V$			500	nA
Peak on-state voltage	$V_{TM}$	$I_{TM}=100mA$		1.7	2.2	V
Critical rate of Rise voltage	$dv/dt$		1000			V/ $\mu$ S
Holding current	$I_H$			200		$\mu$ A

